

isc Silicon PNP Power Transistors

3CD9D

DESCRIPTION

- With TO-3 packaging
- Large collector current
- Low collector saturation voltage
- High power dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

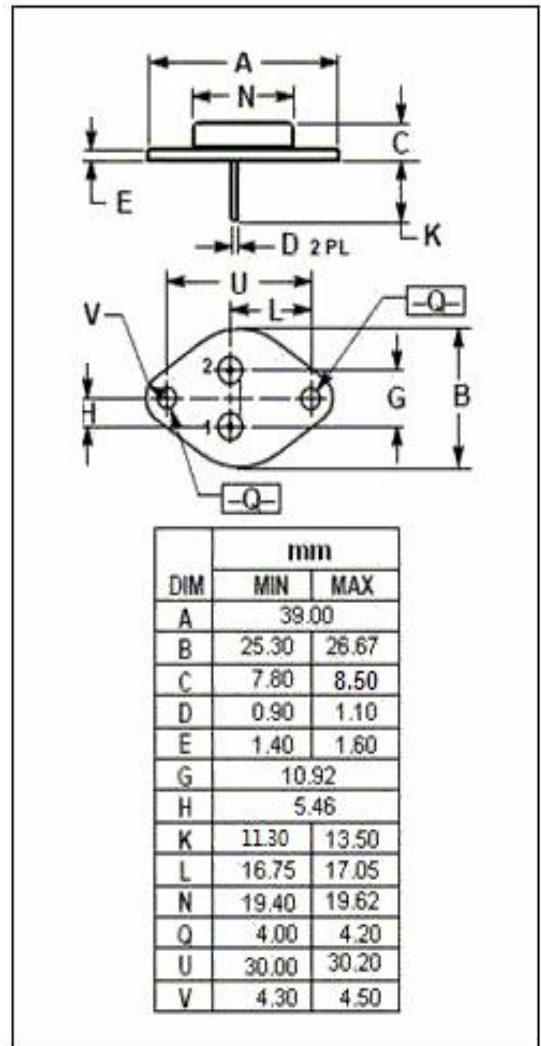
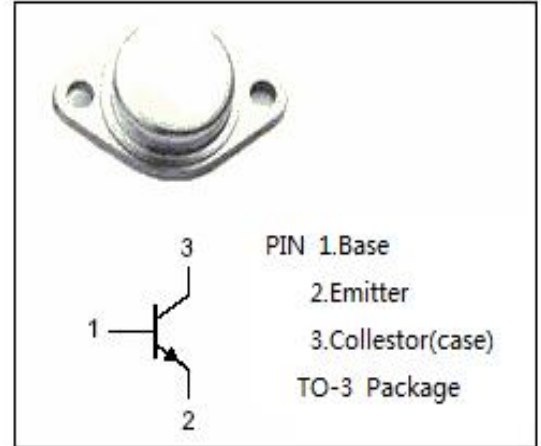
- Designed for use in DC-DC converter
- Driver of solenoid or motor

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-Base Voltage	-110	V
V _{CEO}	Collector-Emitter Voltage	-110	V
V _{EBO}	Emitter-Base Voltage	-4	V
I _c	Collector Current-Continuous	-15	A
P _c	Collector Power Dissipation@T _c =75°C	150	W
T _J	Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature	-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.66	°C/W



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(BR)}	Collector-Emitter Breakdown Voltage	I _C =- 10mA ; I _B = 0	-110		V
V _{EBO(BR)}	Emitter-Base Breakdown Voltage	I _E =- 10mA ; I _C = 0	-4		V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =- 7.5A; I _B = -1.5A		-2	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -7.5A; I _B = -1.5A		-2	V
I _{CEO}	Collector Cutoff Current	V _{CE} =- 110V; I _B = 0		-3.0	mA
I _{CBO}	Collector Cutoff Current	V _{CB} =- 110V; I _E = 0		-1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0		-1.0	mA
h _{FE}	DC Current Gain	I _C = -7.5A; V _{CE} =-10V	10	180	